

(19) World Intellectual Property  
Organization  
International Bureau



(43) International Publication Date  
14 July 2005 (14.07.2005)

PCT

(10) International Publication Number  
**WO 2005/064658 A1**

(51) International Patent Classification<sup>7</sup>: **H01L 21/20**,  
27/12, 29/161, 29/786

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(21) International Application Number:  
PCT/JP2004/018982

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(22) International Filing Date:  
14 December 2004 (14.12.2004)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:  
2003-434021 26 December 2003 (26.12.2003) JP  
2004-265559 13 September 2004 (13.09.2004) JP

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(81) Designated States (unless otherwise indicated, for every kind of national protection available): AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NA, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW.

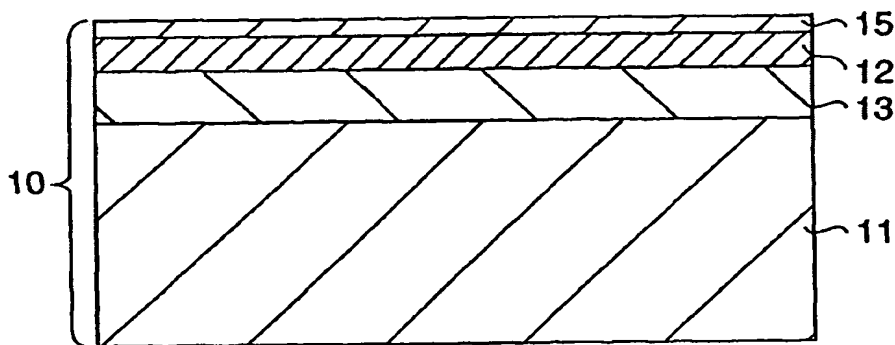
(84) Designated States (unless otherwise indicated, for every kind of regional protection available): ARIPO (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IS, IT, LT, LU, MC, NL, PL, PT, RO, SE, SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Published:

— with international search report

For two-letter codes and other abbreviations, refer to the "Guidance Notes on Codes and Abbreviations" appearing at the beginning of each regular issue of the PCT Gazette.

(54) Title: SEMICONDUCTOR MEMBER, MANUFACTURING METHOD THEREOF, AND SEMICONDUCTOR DEVICE



(57) Abstract: An SiGe layer is grown on a silicon substrate. The SiGe layer or the silicon substrate and SiGe layer are porosified by anodizing the SiGe layer to form a strain induction porous layer or a porous silicon layer and strain induction porous layer. An SiGe layer and strained silicon layer are formed on the resultant structure. The SiGe layer in the stacking growth step only needs to be on the uppermost surface of the porous layer. For this reason, an SiGe layer with a low defect density and high concentration can be formed. Since the SiGe layer on the strain induction porous layer can achieve a low defect density without lattice mismatching. Hence, a high-quality semiconductor substrate having a high strained silicon layer can be obtained.